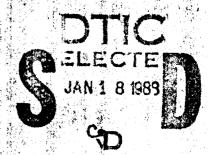
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THE BOUNDARY INTEGRAL METHOD FOR PLANAR MICROSTRIP CIRCUITS

TECHNICAL REPORT

SANCHI SANDY CHANG AND TATSUO ITOH

DECEMBER 1988



ARMY RESEARCH OFFICE
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Abstract

THE BOUNDARY-INTEGRAL METHOD FOR PLANAR MICROSTRIP CIRCUITS

The main subject of this thesis is to develop a general purpose computer program for the analysis containing a planar microstrip circuit arbitrarily shaped. Based on the boundary-integral method (also called the contour-integral method), the analyses of circuits containing right - angled microstrip bend with or without a miter cut and circuits of a T-junctions with or without a V-shaped cut are presented in this thesis. Scattering parameters and other related data of the circuits are calculated and presented. They agree well with published data. It is shown that the boundary-integral method is an applicable and effective computer-aided design tool for microstrip circu's of more complicated geometries.

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Introduction

In the development of microwave integrated circuits (MIC) and millimeter-wave integrated circuits (MMIC), the planar microstrip line technique gained much attention mainly due to the fact that the mode of propagation on the microstrip line is almost TEM. The so called waveguide model has been applied successfully to a number of microstrip discontinuities. Microstrip circuits are often accompanied by discontinuities of one type or another, of which, the most common forms are the right-angled bend and T-junction. The geometries of the circuits analyzed are shown in Figures 1 and Figures 2. In order to simplify the analysis and to make use of well developed waveguide techniques, the microstrip line circuits are usually replaced by equivalent parallel-plate waveguides with magnetic side walls (as shown in Fig.3). After each microstrip line network is replaced with a closed structure, the microstrip discontinuity problem becomes that of a closed waveguide. Due to the discrete nature of modal spectrum in closed structure, the analysis of the scattering from the discontinuity is handled rather easily, typically by a mode - matching method.

There are many methods that can be used to analyze planar circuits, such as eigenvalue method, or the Rayligh-Ritz method. For planar circuits with simple geometrical shapes, like circles or rectangles shapes, the eigenvalue method can be readily used.

The Rayleigh-Ritz method or finite element method on the other hand can be used to solve more complicated planar circuits. However, the computation of eigenfunctions over the entire area of the circuit pattern is time-consuming. The segmentation and desegmentation methods [1][2] can be used to analyze irregular complicated circuits, but there are some limitations on the shapes of such circuits. Details of these methods of analysis as well as their limitations were discussed in more detail in a number of articles [1],[2],[3],[4].

For an arbitrarily shaped planar circuit, using the boundary-integral equation method to develop a general purpose computer program to do the analysis is effective, accurate and adaptable since only the voltage and the current along the periphery of the circuit -- not the entire area of the circuit -- need to be considered. Circuit parameters can be derived from the boundary-integral equation method directly. Hence, analysis of more complicated circuits can be handled easily and the computer time is reduced.

In the next section, this boundary-integral equation method is discribed. The process of program design is also given. In the subsequent section, results based on the formulation are presented in terms of the scattering parameters, and a comparison of results obtained by different numbers of sampling points along the periphery is also presented.

Formulation

Based on the two-dimensional planar circuit presented and introduced in [5], a planar microstrip model with an arbitrary shape is considered. It is filled with material of effective permittivity ε_{re} and the effective width is W_{eff} . There are several coupling ports located around the planar circuits. We divide the circuit periphery into N incremental sections numbered as 1,2,3,....,N, having width W1,W2,W3,....,Wn, respectively. Coupling ports are assumed to occupy two or more sections (as illustrated in Fig.4). Sampling points are set at the center of each section, and the magnetic and electric field intensities are assumed to be constant over each section.

Using Weber's solution for cylindrical waves[6], the potential at each sampling point along the periphery is satisfied by the following matrix equations:

$$\sum_{j=1}^{N} u_{ij} V_{j} = \sum_{j=1}^{N} h_{ij} I_{j}$$
 (1)

$$u_{ij} = 1$$
 (i = j)

$$= \delta_{ij} - \frac{k}{2j} \int_{w_{ij}} \cos \theta_{ij} H_{1}^{(2)}(kr) ds$$
 (2)

$$h_{j} = \frac{\omega \mu d}{4} \frac{1}{W_{j}} \int_{W_{j}} H_{0}^{(2)}(kr) ds$$

$$= \frac{\omega \mu d}{4} \left[1 - \frac{2j}{\pi} \left(\ln \frac{kw_{j}}{4} - 1 + \gamma \right) \right] \qquad (i = j)$$
(3)

$$\gamma = 0.5772....$$
 (Euler's constant) $k=\omega \sqrt{\varepsilon_r \varepsilon_0 \mu_0}$

where $I_j = -2i_n W_j$; the total current flowing into the jth port on both the

upper and lower surfaces of the circuit plates.

 $H_0^{(2)}$, $H_1^{(2)}$: the zeroth order and the first order Hankel function of

the second kind, respectinely.

d: the thickness of dielectric layer.

 \mathbf{r}_{ij} and $\mathbf{\theta}_{ij}$: the distance between the ith and jth coupling ports and

the angle made by the line connecting these points and the normal at the jth sampling point.

The rf voltage of each sampling point can be obtained by solving (1):

$$[V] = U^{-1}H[I]$$
 (4)

$$[V] = [Z]_{nxn}[I]$$
 (5)

$$[\mathbf{Z}]_{\mathbf{n} \times \mathbf{n}} = \mathbf{U}^{-1} \mathbf{H} \tag{7}$$

[Z] is an nxn matrix. It is considered that all n sections are coupling ports. In fact, most of the n ports described above are open circuits; in other words, most of the nxn elements of $[Z]_{nxn}$ are zero. Therefore $[Z]_{nxn}$, can be reduced by choosing only the necessary elements given by (7). The reduced matrix $[Z]_{nxn}$ is described in (8). N is the sum of all sampling points along all A ports. (As shown in Fig.5)

$$N = \sum_{i=1}^{A} m_i$$

m: the number of sampling points of ith port

$$[V] = [Z]_{NxN}[I]$$
(8)

The next step is to consider the higher order modes of each port by expanding the RF voltage and current density of each port in terms of m stripline modes.

$$V(X_K^{(i)}) = \sum_{L=1}^{m_i} v_L^{(i)} \cos[(L-1) \frac{X_K^{(i)} \pi}{w_i}]$$
 (10)

$$I(X_K^{(i)}) = \sum_{L=1}^{m_i} \frac{1}{m_i} v_L^{(i)} \cos[(L-1) \frac{X_K^{(i)} \pi}{w_i}]$$
 (11)

 $X_K^{(i)}$: kth sampling point at the ith port

$$k = 1,2,...,m$$
 $i = 1,2,...,A$

 \mathbf{V}_{L} : magnitude of modal voltageat each sampling point

$$(i = 1,2,...,A)$$

W_i: width of the ith port

From Fig.5, we obtain the point

$$X_K^{(i)} = \frac{w_i}{2m_i} + \frac{w_i(k-1)}{m_i} = \frac{w_i(2k-1)}{2m_i}$$

So, equations (10) and (11) can be witten as follows:

$$V(X_K^{(i)}) = \sum_{L=1}^{m_i} v_L^{(i)} \cos\left[\frac{(L-1)\pi(2k-1)}{2m_i}\right]$$
 (12)

$$I(X_K^{(i)}) = \sum_{L=1}^{m_i} \frac{1}{m_i} v_L^{(i)} \cos\left[\frac{(L-1)\pi(2k-1)}{2m_i}\right]$$
 (13)

and then

$$V(X_1^{(1)}) = v_1^{(1)} + v_2^{(1)} \cos(\frac{\pi}{2m_1}) + \dots + v_{m_1}^{(1)} \cos(\frac{(m_1-1)\pi}{2m_1})$$

$$V(X_{k}^{(1)}) = v_{1}^{(1)} + v_{2}^{(1)} cos(\frac{(2k-1)\pi}{2m_{1}}) + \dots + v_{m_{1}}^{(1)} cos(\frac{(2k-1)(m_{1}-1)\pi}{2m_{1}})$$

$$V(X_{m_{1}}^{(1)}) = v_{1}^{(1)} + v_{2}^{(1)} cos(\frac{(2m_{1}-1)\pi}{2m_{1}}) + \dots + v_{m_{1}}^{(1)} cos(\frac{(2m_{1}-1)(m_{1}-1)\pi}{2m_{1}})$$

$$V(X_1^{(A)}) = v_1^{(A)} + v_2^{(A)} cos(\frac{\pi}{2m_A}) + \dots + v_{m_A}^{(A)} cos(\frac{(m_A-1)\pi}{2m_A})$$

$$V(X_{k}^{(A)}) = v_{1}^{(A)} + v_{2}^{(A)} \cos(\frac{(2k-1)\pi}{2m_{A}}) + \dots + v_{m_{A}}^{(A)} \cos(\frac{(2k-1)(m_{A}-1)\pi}{2m_{A}})$$

$$V(X_{m_A}) = v_1^{(A)} + v_2^{(A)} cos(\frac{(2m_A-1)\pi}{2m_A}) + \dots + v_{m_A}^{(A)} cos(\frac{(2m_A-1)(m_A-1)\pi}{2m_A})$$

(14)

$$I(X_1^{(1)}) = \frac{1}{m_1} \left(i_1^{(1)} + i_2^{(1)} \cos(\frac{\pi}{2m_1}) + \dots - i_{m_1}^{(1)} \cos(\frac{(m_1 - 1)\pi}{2m_1}) \right)$$

$$I(X_k^{(1)}) = \frac{1}{m_1} \left(i_1^{(1)} + i_2^{(1)} \cos(\frac{(2k-1)\pi}{2m_1}) + \dots + i_{m_1}^{(1)} \cos(\frac{(2k-1)(m_1-1)\pi}{2m_1}) \right)$$

$$I(X_{m_1}^{(1)}) = i_1^{(1)} + i_2^{(1)} \cos(\frac{(2m_1 - 1)\pi}{2m_1}) + \dots + i_{m_1}^{(1)} \cos(\frac{(2m_1 - 1)(m_1 - 1)\pi}{2m_1})$$

$$I(X_1^{(A)}) = \frac{1}{m_A} \left(i_1^{(A)} + i_{(A),2} \right) \cos\left(\frac{\pi}{2m_A}\right) + \dots + i_{m_A}^{(A)} \cos\left(\frac{(m_A-1)\pi}{2m_A}\right) \right)$$

$$I(X_{k}^{(A)}) = \frac{1}{m_{A}} \left(i_{1}^{(A)} + i_{2}^{(A)} \cos(\frac{(2k-1)\pi}{2m_{A}}) + \dots + i_{m_{A}}^{(A)} \cos(\frac{(2k-1)(m_{A}-1)\pi}{2m_{A}}) \right)$$

$$I(X_{m_A}^{(A)}) = \frac{1}{m_A} \left(i_1^{(A)} + i_2^{(A)} \cos(\frac{(2m_A - 1)\pi}{2m_A}) + \dots + i_{m_A}^{(A)} \cos(\frac{(2m_A - 1)(m_A - 1)\pi}{2m_A}) \right)$$

(15)

(16)

$$\begin{pmatrix}
v(x)^{(1)} \\
v(x)^{(2)} \\$$

$$\begin{pmatrix}
v(x)^{(1)} \\
v(x)^{(1)} \\
v(x)^{(1)} \\
v(x)^{(2)} \\$$

$$A^{(1)} = \begin{pmatrix} 1 & \cos\left(\frac{\pi}{2m_1}\right) & \dots & \cos\left((m_1 - 1)\frac{\pi}{2m_1}\right) \\ 1 & \cos\left(\frac{3\pi}{2m_1}\right) & \dots & \cos\left((2m_1 - 1)\frac{\pi}{2m_1}\right) \\ 1 & \cos\left((2m_1 - 1)\frac{\pi}{2m_1}\right) & \dots & \cos\left((2m_1 - 1)(m_1 - 1)\frac{\pi}{2m_1}\right) \end{pmatrix}$$

$$A^{(i)} = \begin{pmatrix} 1 & \cos\left(\frac{\pi}{2m_i}\right) & \dots & \cos\left((m_1 - 1)\frac{\pi}{2m_i}\right) \\ 1 & \cos\left(\frac{3\pi}{2m_i}\right) & \dots & \cos\left((2m_1 - 1)\frac{\pi}{2m_i}\right) \\ 1 & \cos\left((2m_1 - 1)\frac{\pi}{2m_i}\right) & \dots & \cos\left((2m_1 - 1)(m_1 - 1)\frac{\pi}{2m_i}\right) \end{pmatrix}$$

$$A^{(A)} = \begin{pmatrix} 1 & \cos\left(\frac{\pi}{2m_A}\right) & \dots & \cos\left((2m_1 - 1)(m_1 - 1)\frac{\pi}{2m_A}\right) \\ 1 & \cos\left((2m_1 - 1)\frac{\pi}{2m_A}\right) & \dots & \cos\left((2m_1 - 1)\frac{\pi}{2m_A}\right) \\ 1 & \cos\left((2m_1 - 1)\frac{\pi}{2m_A}\right) & \dots & \cos\left((2m_1 - 1)\frac{\pi}{2m_A}\right) \end{pmatrix}$$

$$A^{(1)} = \begin{pmatrix} 1 & \cos\left(\frac{3\pi}{2m_A}\right) & \dots & \cos\left((2m_1 - 1)(m_1 - 1)\frac{\pi}{2m_A}\right) \\ 1 & \cos\left((2m_1 - 1)\frac{\pi}{2m_A}\right) & \dots & \cos\left((2m_1 - 1)(m_1 - 1)\frac{\pi}{2m_A}\right) \end{pmatrix}$$

$$M^{(1)} = \begin{pmatrix} \frac{1}{m_1} & \dots & \frac{1}{m_1} \\ \vdots & \vdots & \vdots \\ \frac{1}{m_1} & \dots & \frac{1}{m_1} \\ \vdots & \vdots & \vdots \\ \frac{1}{m_1} & \dots & \frac{1}{m_1} \end{pmatrix}$$

$$m_1 \times m_1$$

$$M^{(2)} = \begin{pmatrix} \frac{1}{m_2} & \frac{1}{m_2} \\ \vdots & \vdots \\ \frac{1}{m_2} & \frac{1}{m_2} \\ m_2 \times m_2 \end{pmatrix}$$

$$M^{(A)} = \begin{pmatrix} \frac{1}{m_A} & \frac{1}{m_A} \\ \vdots & \vdots \\ \frac{1}{m_A} & \frac{1}{m_A} \\ \vdots & \vdots \\ \frac{1}{m_A} & \frac{1}{m_A} \end{pmatrix}$$

$$m_A \times m_A$$

$$(19)$$

$$[V] = [Z]_{NxN}[I]$$
 (20)

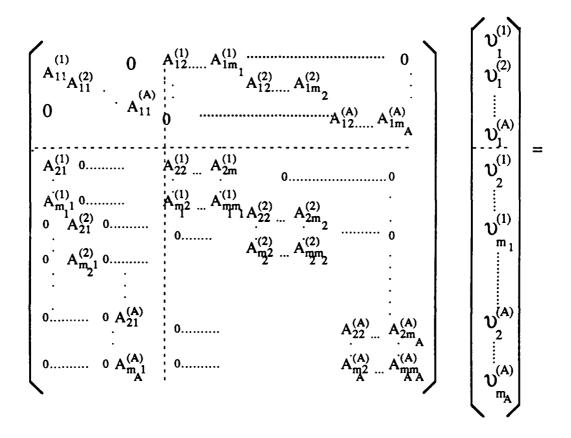
$$[A][V] = [Z][A][M][i]$$
 (21)

[U] and [i] are Nx1 matrices
[Z], [A] and [M] are NxN matrices

We define
$$[B] = [Z][A][M]$$

$$[A][V] = [B][i]$$
(22)

For the purpose of separating the first order mode from higher order modes, the matrices [A], [B] are rearranged as below:



$$\begin{bmatrix} B_{11} & B_{1,N-m+1} & B_{12} & B_{1,N-m+2} & B_{1N} \\ B_{11} & B_{1,N-m+1} & B_{12} & B_{1,N-m+2} & B_{1N} \\ B_{11} & B_{1,N-m+1} & B_{1,N-m+1} & B_{1,N-m+1,2} & B_{1,N-m+2} & B_{1,N-m+1,N} \\ B_{21} & B_{2,m+1} & B_{2,N-m+1} & B_{22} & B_{2m} & B_{2,N-m+2} & B_{2N} \\ B_{m1} & B_{m,N-m+1} & B_{m,2} & B_{m,m} & B_{m,n-m+2,N-m+2} & B_{n-m+2,N-m+2,N-m+2} \\ B_{N1} & B_{N,N-m+1} & B_{N2} & B_{N,N-m+2} & B_{N,N-m+2} & B_{N-m+2,N-m+2} \\ B_{N1} & C_{21} & C_{22} & V_{2} & D_{21} & D_{22} & I_{2} \\ \end{bmatrix} \begin{bmatrix} i & (1) & i &$$

$$\mathbf{C}_{11} = \begin{bmatrix} \mathbf{A}_{11}^{(1)} & \mathbf{0} \\ \mathbf{A}_{11}^{(2)} & \mathbf{A}_{11}^{(A)} \\ \mathbf{0} & \mathbf{A}_{11}^{(A)} \end{bmatrix} \mathbf{C}_{12} = \begin{bmatrix} \mathbf{A}_{12}^{(1)} & \mathbf{A}_{1m_{1}}^{(1)} & \cdots & \mathbf{0} \\ \mathbf{A}_{12}^{(2)} & \mathbf{A}_{1m_{2}}^{(2)} & \mathbf{A}_{1m_{2}}^{(2)} & \mathbf{A}_{1m_{2}}^{(A)} \\ \mathbf{0} & \cdots & \mathbf{A}_{12}^{(A)} & \mathbf{A}_{1m_{A}}^{(A)} \end{bmatrix}$$

$$D_{21} = \begin{pmatrix} B_{21} & B_{2,\vec{m}_1} + 1 \cdots & B_{2,N-m+1} \\ \vdots & \vdots & \vdots & \vdots \\ B_{m-1} & \vdots & B_{m-1} + N-m+1 \\ \vdots & \vdots & \vdots & \vdots \\ B_{N-m+2,1} & B_{N-m+2,N-m+1} \\ \vdots & \vdots & \vdots & B_{N-m+2,N-m+1} \end{pmatrix}$$

$$D_{12} = \begin{pmatrix} B_{12} & B_{12} & \dots & B_{N-m+2,N-m+1} \\ \vdots & \vdots & \vdots & \vdots \\ B_{N-m+1,2} & B_{N-m+1,m} & B_{N-m+1,N} \\ \vdots & \vdots & \vdots & \vdots \\ B_{m_1} & B_{m-1} & B_{N-m+2,N-m+2} & B_{2N} \\ \vdots & \vdots & \vdots & \vdots \\ B_{N-m+2,2} & B_{N-m+2,m} & B_{N-m+2,N-m+2} & B_{N-m+2,N} \\ \vdots & \vdots & \vdots & \vdots \\ B_{N2} & B_{Nm} & B_{Nm} & B_{N,N-m+2} & B_{NN} \end{pmatrix}$$

An important property of waveguide modes is the existence of a characteristic wave impedance. From the field theory point of view, each possible solution to the wave equation is called a mode. A TEM wave is called a transmission-line mode, and all other waves are called higher-order modes.

When assuming that the stripline is straight with sufficient length, only the TEM mode can propagate in the uniform stripline, and higher-order modes which exist at the port i are considered to be loaded by the reactive characteristic impedance matrix [$\mathbf{Z}_{L}^{(i)}$]_{(\mathbf{m}_{i} -1)x(\mathbf{m}_{i} -1).}

$$[v_{L}^{(i)}]_{(m_{i}-1)\times 1} = [\mathbf{Z}_{L}^{(i)}]_{(m_{i}-1)\times (m_{i}-1)} [i_{L}^{(i)}]_{(m_{i}-1)\times 1}$$

$$L = 2,3,....,m_{A}$$

$$i = 1,2,....,A$$
(25)

$$[\mathbf{Z}_{L}^{(i)}]_{pq} = -j\mathbf{Z}_{c}\{((L-1)\lambda/2W_{e}\sqrt{\epsilon_{re}})^{2} 1\}^{-1/2} \quad (p=q)$$
 (26)

= 0 (27)
p, q = 1,2,3,...,
$$m_i$$
 -1 $i = 1,2,...,A$

$$\mathbf{z}_{c} = \frac{120\pi d}{W_{e}\sqrt{\varepsilon_{re}}}$$
 (28)

d: the thickness of the substructure

W_e: the effective width of the stripline

Ere: the effective relative dielectric constant

Then, we can find the relative equation for the higher order modes at each port.

$$V_2 = Z_L I_2 \tag{31}$$

Based on analysis using contour-integral method, $[Z]_{AxA}$ (shown as Eq.44) the fundmental modes of the network at port 1,2,...,A can be extracted from TEM modes and loaded by the characteristic impedances of the higher order modes. $[Z]_{AxA}$ can be transformed into the scattering matrix (shown as Eq.46) directly as follows.

$$C_{11}V_1 + C_{12}V_2 = D_{11}I_1 + D_{12}I_2$$
 (32)

$$C_{21}V_1 + C_{22}V_2 = D_{21}I_1 + D_{22}I_2$$
 (33)

$$V_2 = Z_1 I_2 \tag{34}$$

$$C_{11}V_1 + C_{12}Z_1I_2 = D_{11}I_1 + D_{12}I_2$$
(35)

$$C_{21}V_1 + C_{22}Z_LI_2 = D_{21}I_1 + D_{22}I_2$$
(36)

$$C_{11}V_{1} = D_{11}I_{1} + (D_{12} - C_{12}Z_{L})I_{2}$$
 (37)

$$C_{21}V_1 = D_{21}I_1 + (D_{22} - C_{22}Z_1)I_2$$
 (38)

$$C_{11}V_1 + (C_{12} - D_{12}Z_L^{-1})V_2 = D_{11}I_1$$
(39)

$$C_{21}V_1 + (C_{22} \cdot D_{22}Z_L^{-1}) V_2 = D_{21}I_1$$
 (40)

from (39),(40)

$$(C_{22} - D_{22}Z_L^{-1}) V_2 = -C_{21}V_1 + D_{21}I_1$$
 (41)

$$V_{2} = -(C_{22} - D_{22}Z_{L}^{-1})^{-1}C_{21}V_{1} + (C_{22} - D_{22}Z_{L}^{-1})^{-1}D_{21}I_{1}$$
(42)

substitute (42) into (39)

$$[C_{11} - (C_{12} - D_{12}Z_L^{-1}) (C_{22} - D_{22}Z_L^{-1})^{-1}C_{21}]V_1 =$$

$$[D_{11} - (C_{12} - D_{12}Z_{L}^{-1}) (C_{22} - D_{22}Z_{L}^{-1})^{-1}D_{21}]I_{1}$$
(43)

$$[Z]_{A\times A} = [C_{11} - (C_{12} - D_{12}Z_{L}^{-1})(C_{22} - D_{22}Z_{L}^{-1})^{-1}C_{21}]^{-1}$$

$$[D_{11} - (C_{12} - D_{12}Z_{L}^{-1})(C_{22} - D_{22}Z_{L}^{-1})^{-1}D_{21}]$$
(44)

$$[Z]_{AxA} = \begin{pmatrix} Z_{11} & \cdots & Z_{1A} \\ Z_{21} & \vdots & \vdots \\ Z_{A1} & \cdots & Z_{AA} \end{pmatrix}$$

$$(45)$$

$$[S] = [\sqrt{Y_0}]([Z] - [Z_0])([Z] + [Z_0])^{-1}[\sqrt{Z_0}]$$
(46)

$$[Y_0] = 1/[Z_0] \tag{48}$$

Numerical results

1. Right-angled bend with and without a miter cut: (Fig.1 a.b)

Shown in Fig.6 is the variation in the reflection coefficient $|s_{11}|$ for chamfered and unchamfered right-angle bends. The results are compared with Gupta's results [9]. In order to reduce the effect of the discontinuity reactances, an isosceles triangle part must be removed. The size of the triangle removed has been optimized, to minimize the reflection coefficient. Figure 7 shows that when a measured cut ratio c/w is equal to about 0.8, the V.S.W.R. is minimized. Kaneko has the same conclusions[7].

2. T-junction without a miter cut: (Fig. 2a)

Results for frequency dependent scattering matrix coefficients for a T-junction ($\xi = 9.7$, d = 0.0635 cm, w₂=0.056 cm) are shown in Fig.8. It notes that $|s_{22}|$, as shown in Fig.8a, the power reflected by the T-junction discontinuities increases with frequency in the range $0 < f < f_{c1}$, where $|f_{c1}|$ is the cut-off frequency of the first higher order mode. Correspondingly, the power transmitted from port 1 to port 2 decreases with frequency greater than $|f_{c1}|$. The power of a port is transmitted by the first higher order mode, so that the transmission coefficient $|s_{c1}|$ is always smaller than that for $|f_{c1}|$ (shown in Fig.8b).

Fig.8c indicates that, if the TEM mode is incident at port 1, the reflected power decreases with increasing frequency, and another power transmitted to port 3 behaves in an opposite sense to | s₁₂|. Also plotted in Fig.8 are the numerical results reported in [8].

3. T - junction with a V - shaped miter cut: (Fig. 2b)

This section considers a T-junction with an isosceles triangle with angle $\theta = 45^{\circ}$ removed; the side of the triangle removed is equal to c (cut depth). For a cut ratio c/w2 = 0.4035..., the scattering coefficients are plotted in Fig.9. The reported data [9] is also plotted in fig.9. When the frequency increases, the variation of the magnitude of reflected coefficient $|\mathbf{s}_{1}|$ keeps almost constant and is between a range of 0.41 to 0.45. The predicted value of $|\mathbf{s}_{2}|$ is greater than the published value by 2.5 percent.

For different cut ratios, Fig. 10 shows clearly that by removing an isosceles triangle from a T - junction with $\theta = 45 \text{ s}(0,)$ and c/w2 = 0.8, the effects of $|s_{11}|$ are minimized at the higher frequency band. This phenomenon is similar to the case of right-angled microstrip bend with a miter cut ratio 0.8. By considering a plane of symmetry located at half the width of port 2, the T-junction can be compared with a right-angled bend on just one side of the symmetrical plane. The reflection coefficient $|s_{11}|$ is equal to $|s_{33}|$ of the corresponding side of the bend. Thus, if only $|s_{11}|$ or $|s_{33}|$ is to be optimized, then only a right-angled bend with one half of the width of port 2 need to be considered.

In the boundary - integral method, the circuit periphery is divided into N sections, the value of N determines the size of NxN impedance matrix [Z]. The greater N is, the more precise the result will be. The error decreases from 8 to 2.5 percent with N increased from 80 to 300 (Fig.11). Also, for the purpose of saving computer time, the problem of properly selecting the location of each scattering point become more important when the effective width of each port is not the same.

Conclusion

Computer-aided-design is a very powerful tool in the circuit design of MIC and MMIC. A great savings of time and money can be resulted if a design is verified before it is fabricated. The work described in this paper showed how the boundary-integral method can be used to solve planar microstrip circuits. The results discussed here are in excellent agreement with other methods for the right-angled bend and T-junction. Future studies will concentrate on developing this method for more complicated microstrip discontinuities.

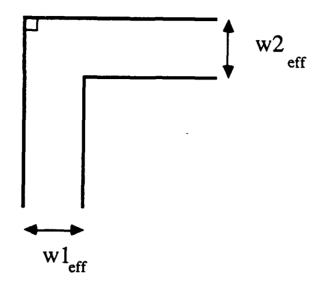


Fig. 1a

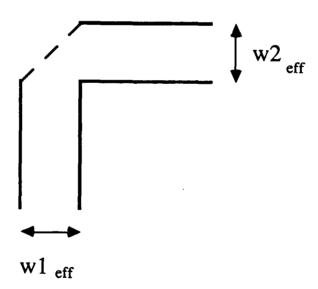
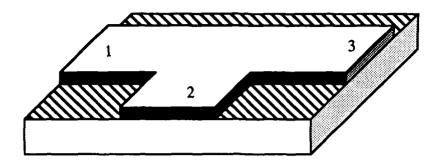
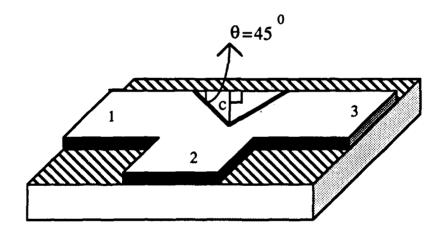


Fig. 1b



Microstrip T- junction structure Fig. 2a



T-junction microstrip with a V-shape cut

Fig. 2b

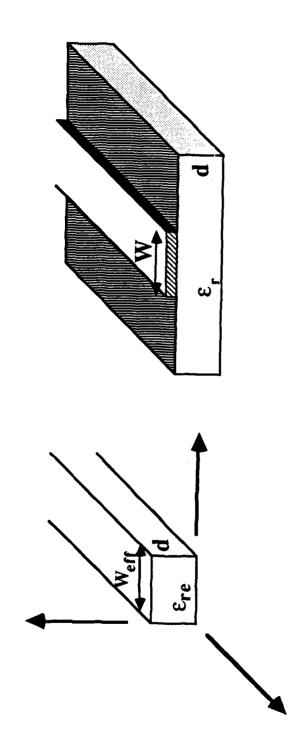


Fig. 3

Sampling points

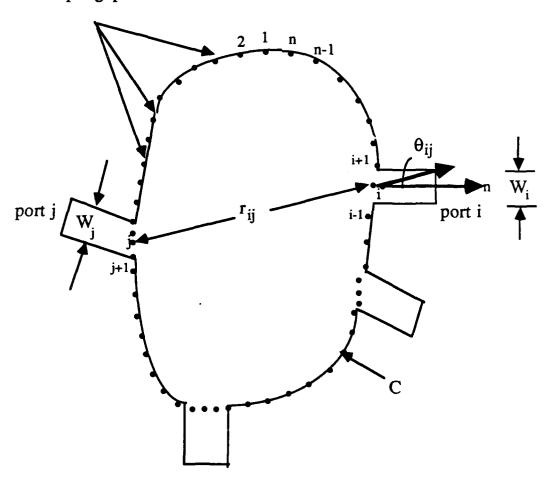
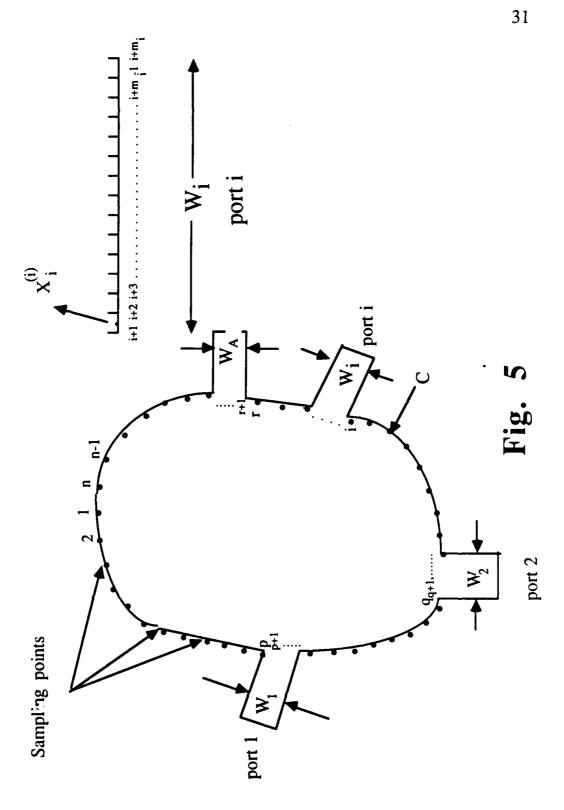


Fig. 4



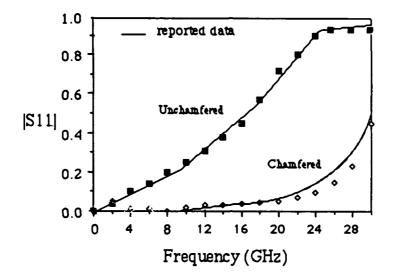
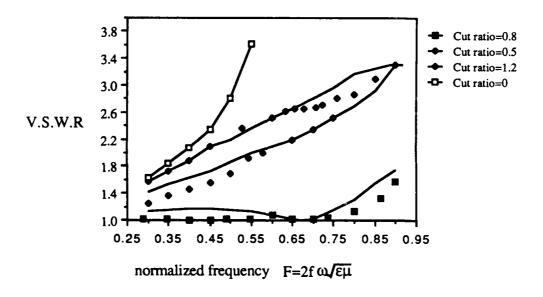
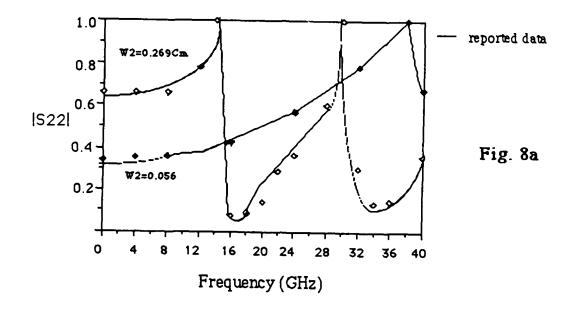


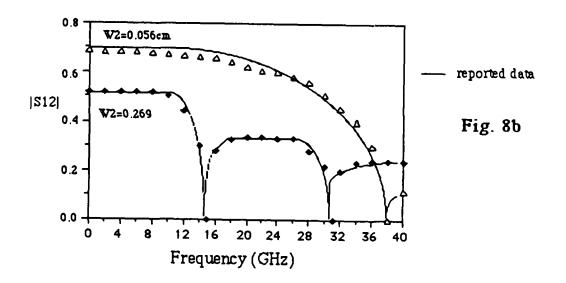
Fig. 6

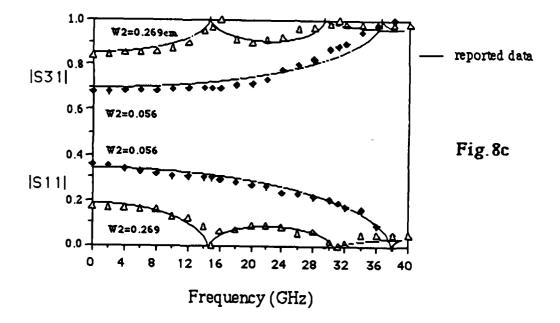


 $W1_{\text{eff}} = W2_{\text{eff}} = 0.056 \text{cm,d} = 0.0635 \text{cm,} \epsilon_{\text{r}} = 9.7$

Fig. 7







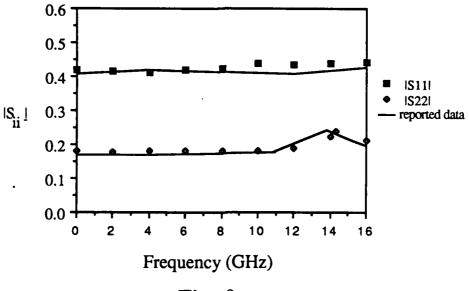


Fig. 9

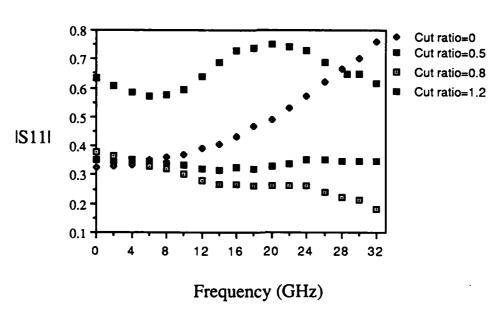


Fig. 10

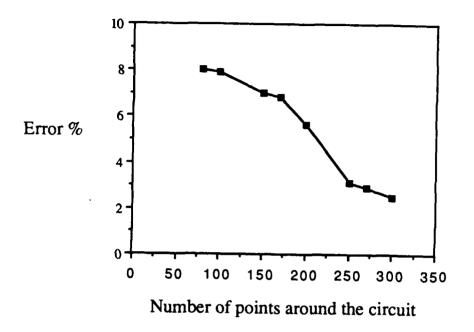


Fig. 11

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